

Pulsed Power system

PI

Prerequisite courses:

Electric Circuits.

Engineering Mathematics / Phys Mathematics (ODE)

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② * No office hour, please feel free to stop by my office whenever my door is open & nobody is in my office. Or you may email me to schedule a meeting.

③ * Class time : 9:10 ~ 12:00 English
→ 9:10 ~ 11:30 ~~class~~ with 10 mins break
11:30 ~ 12:00 ~~class~~ Mandarin for P&R.

④ * Assignments : 70% → No roll call.
Presentations : 30%

⑤ * References: Pulsed power systems by H. Bluhm.
Circuit analysis by Cunningham and Stuller

* Additional References:

Pulsed Power by Gennady A. Mesyats

J. C. Martin on Pulsed Power

* Class material: myweb.neku.edu.tw/~pchang

* Course Outline:

- Introduction to pulsed-power system. - (9/14) → 9/21. p2
- Review of circuit analysis - 9/21. ← HW. of KLC circuits

72. Static and dynamic breakdown strength of dielectric material. - 9/28, 10/5

- Gas. → avalanche, Townsend condition, Paschen Law. * HW?
- Liquid
- Solid.

73 Energy storage. 10/12 - 10/19.

- pulsed discharge capacitors
- Marx generators.
- Inductive energy storage.

← HW. of explory Marx

74 Switches. 10/26 - ~~11/2~~ 11/9

- Closing switches → gas switches
- Opening switches →

← calculate capacitor safety possession eq.

75 Pulse-forming networks ~~11/9~~; ~~11/16~~ 11/23
11/16

- Transmission lines
- RLC networks

76 Pulse transmission and transformation ~~11/22~~ - ~~11/30~~ 12/17
11/30

- self-magnetic insulation in vacuum lines
- pulse transformers
- High voltage power supply
- Transformation lines

37. Power and voltage adding

~~12/14~~ 12/14

P3

- └ Addng of power
- └ voltage adding

39.

Diagnostics

12/21, 12/28.

- └ Electromagnetic - Field sensors
 - └ Capacitive sensor
 - └ Inductive
- └ Current-viewing resistors (CURS)
- └ Current measurements based on Faraday Effect.
- └ E-field - - - - - Electro-optic effects.
- └ Magnetic ion energy analysers
- └ Vacuum voltage monitors

310. Applications of pulsed-power system 1/4

3

7 Introduction to pulsed-power system 24

* Pulsed power is a scheme where stored energy is discharged as electrical energy into a load in a short pulse or ~~as~~ short pulses with a controllable repetition rate.

⇒ Example of pulsed power in daily life:

- Driven piles

- Hammer.

- making ~~sticky~~ rice cake. → great example of short pulses with a controllable repetition rate.

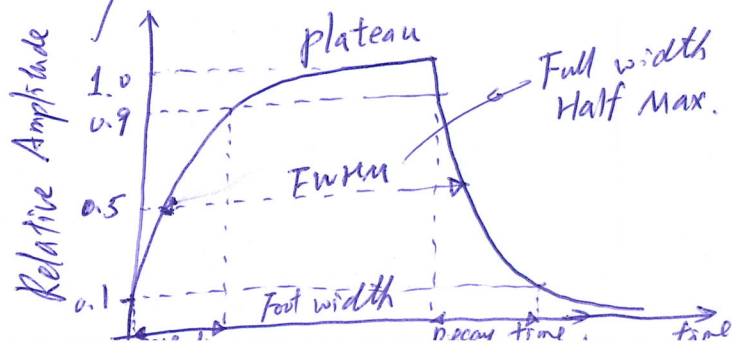
* Pulsed power in general: $P \sim 10^9 \text{ W (1 GW)}$
 $E \geq \text{kJ}$

The highest energy and power that have been achieved in a single pulse are in the order of 100 MJ & few hundred TW, respectively.

- $V: 10 \text{ kV} \sim 50 \text{ MV}$

$I: 1 \text{ kA} \sim 10 \text{ MA}$.

* A pulse is characterised by its shape, i.e., by its rise ~~time~~ & fall times and by the duration and flatness of its plateau region



- Pulse rise time - the time it takes the voltage to rise from 10% to 90%. PS

- Pulse } fall time - - - - - fall
 } decay 90% to 10%.

- Both the fall and the rise time of a pulse depend on the evolution of the "Load impedance," which in most cases varies with time.

- pulse duration - no unique definition.

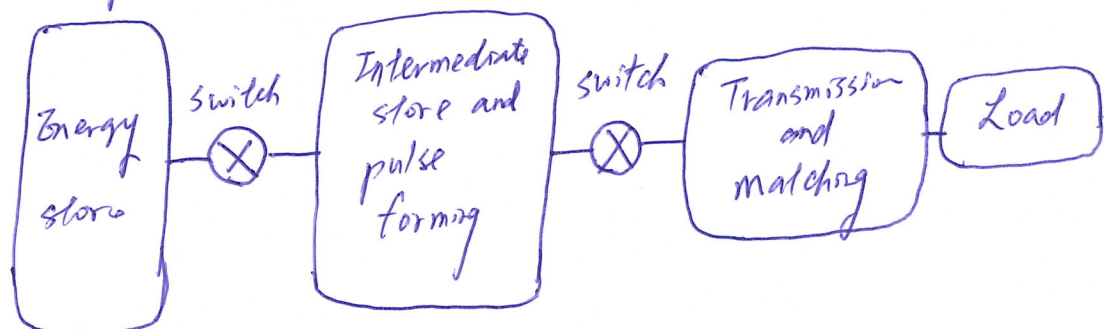
↳ ① FWHM

② ~~Sometimes~~ It is defined as the duration at 90% of the peak amplitude.

③ Flatness of the plateau region is an important requirement for driving some ~~low~~ loads, such as Pocket cells.

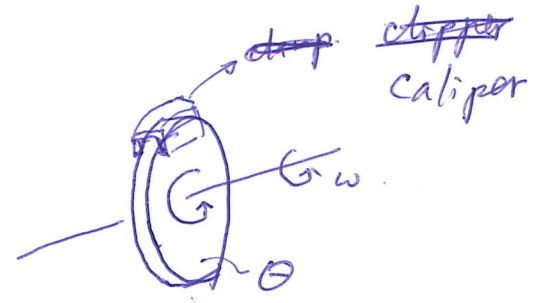
- A ~~general~~ generator scheme for the production of high-power electrical pulses is always based on an energy store that is charged slowly at a relatively low charging power and ~~is~~ is discharged rapidly by acting a switch

- To achieve the desired power magnification factor and to shape the pulse, the above process can be repeated several times.



* The energy can be stored either chemically, mechanically, Pb. or electrically.

Ex: Mechanical energy:



$$W_{kin} = \frac{1}{2} \Theta \omega^2$$

\uparrow moment of inertia \swarrow angular frequency

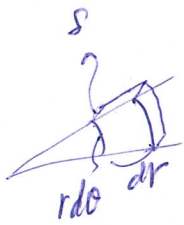
For a massive cylinder: $\Theta = \frac{1}{2} M R^2$

\uparrow mass \swarrow radius

$$\Rightarrow W_{kin} = \frac{1}{2} \cdot \frac{1}{2} M R^2 \cdot \omega^2$$

\Rightarrow Stored energy density: $\omega = \frac{W_{kin}}{M} = \frac{1}{4} R^2 \omega^2$

- The ultimate energy density is limited by the tensile strength of the material used to construct the rotor.



$$d\Sigma = \frac{dF}{A} = \frac{(r d\theta s dr \rho) \cdot r \omega^2}{r d\theta \cdot s}$$

$$= \rho \omega^2 r dr$$

$$\Sigma = \int_0^k \rho \omega^2 r dr$$

$$= \frac{1}{2} \rho \omega^2 k^2$$

$$\Sigma = \int \omega_{max}^2 \frac{r^2}{2}$$

\uparrow tensile strength

for a stainless steel cylinder or radius 1m.

$\omega_{max} = 400 / \text{sec}$ AISI 302 stainless steel

$\Sigma = 520 / 860 \text{ MPa}$

\uparrow yield strength \swarrow ultimate tensile strength

$$\rho = 8.19 \text{ g/cm}^3 = 8190 \text{ kg/m}^3$$

$$\Rightarrow \omega = \sqrt{\frac{2 \Sigma}{\rho r^2}} = \sqrt{\frac{2 \cdot 860 \times 10^6}{8190 \cdot 1}} = 458 \sim 400$$

$$W_{kin} = \frac{1}{4} R^2 \omega^2 = \frac{1}{4} \cdot 1^2 \cdot 400^2 = 4 \times 10^4 \text{ J/kg}$$

high strength alloy ASTM A514 steel

$\rho = 7.8 \text{ g/cm}^3$ $\Sigma = 690 / 760 \text{ MPa}$

\uparrow yield strength \swarrow ultimate tensile strength

$$\omega = \sqrt{\frac{2 \cdot 690 \times 10^6}{7800 \cdot 1^2}} = 420 \sim 400 / \text{sec}$$

$$W_{kin} = \frac{1}{4} R^2 \omega^2 = \frac{1}{4} \cdot 1 \cdot 400^2 = 4 \times 10^4 \text{ J/kg} = 3.1 \times 10^8 \text{ J/m}^3$$

- The problem with mechanical storage is to release the energy in a sufficiently short time. p7

→ Several electrical compression stages are needed in combination with the mechanical storage to achieve the desired power level.

Ex: Electrical energy can be stored either capacitively in an electric field or inductively in a magnetic field.

Sol: Electric field:

$$W_e = \frac{1}{2} \epsilon \cdot \epsilon_0 E^2$$

for oil impregnated paper: $\epsilon = 6$, breakdown strength $E = 0.98 \times 10^8 \text{ V/m}$

$$\Rightarrow W_e = \frac{1}{2} \cdot 6 \cdot 8.85 \times 10^{-12} \cdot (0.98 \times 10^8)^2 = 161 \text{ kJ/m}^3$$

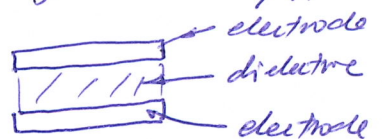
With the finite packing density:

$$E \quad \text{or} \quad W_e = \frac{1}{2} C V^2, \quad C = \epsilon \epsilon_0 \frac{A}{d}$$

$\Rightarrow d \uparrow, W_e \uparrow \rightarrow$ space is ~~not~~ occupied by the electrode.

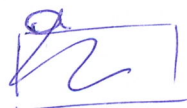
\Rightarrow to estimate the energy storage in space

$$W_e' \approx \frac{1}{2} \times W_e \approx 80 \text{ kJ/m}^3$$



Ex 2: Magnetic field:

$$W_B = \frac{1}{2} \mu_0 \mu_r \frac{B^2}{2\mu_0}$$



The maximum energy density is limited by the onset of melting at the conductor surface or by the mechanical strength of the storage inductor.

$$C_p \cdot \rho \cdot T = \frac{B^2}{2\mu_0} \Rightarrow \frac{1}{2\mu_0} B^2 \Rightarrow$$

↑ heat capacity per unit mass mass density surface temperature

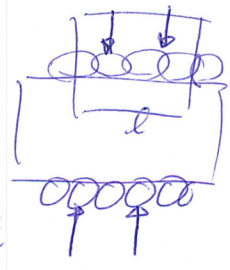
→ a factor of order unity depending on the form of the pulse

$$B \cdot l = \mu_0 N I$$

$$\Rightarrow B = \mu_0 N I \propto I$$

$$E = P \cdot t = I^2 \cdot R \cdot t \propto B^2 \cdot R \cdot t$$

$$\Rightarrow C_v \rho T = \frac{1}{2\mu_0} B^2 \rho \cdot t \approx \frac{B^2}{2\mu_0} \quad \text{take } \rho = 1$$



$$B^2 \approx \sqrt{2\mu_0 \cdot C_v \rho \cdot T} = \sqrt{2 \times 4\pi \times 10^{-7} \times \frac{0.385 \text{ J}}{10^3 \text{ kg} \cdot \text{K}} \times 8960 \cdot (1085 - 25)}$$

Copper: $C_v = 0.385 \text{ J/g} \cdot \text{K} = 96 \text{ J} \approx 100 \text{ J}$

melting: $T = 1085 \text{ }^\circ\text{C}$
 $\rho = 8.96 \text{ g/cm}^3 = 8960 \text{ kg/m}^3$

$P_B \leq \Sigma$ - yield strength $\Sigma = 70 \text{ MPa}$ for Cu

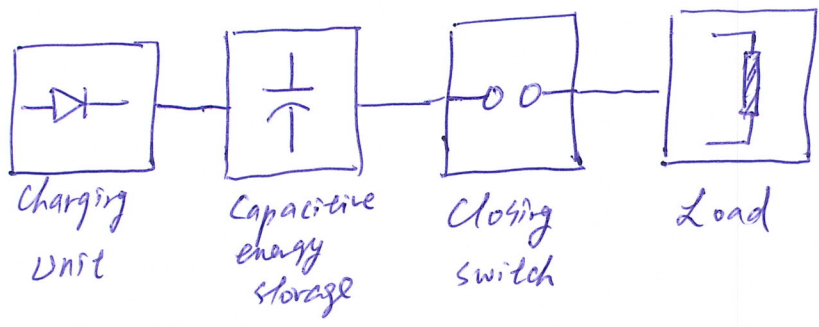
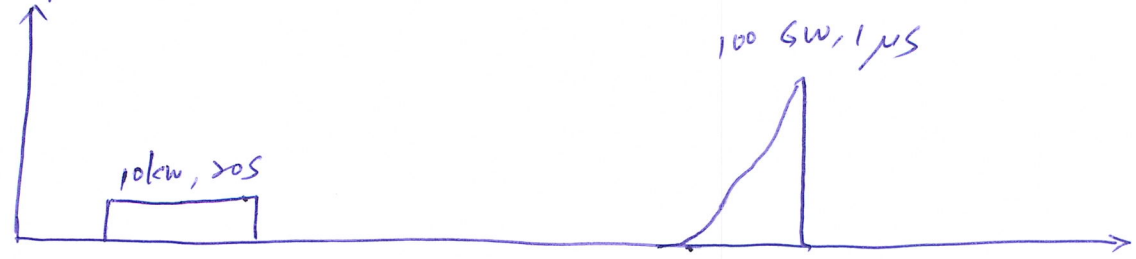
$$\Rightarrow \frac{B^2}{2\mu_0} \leq \Sigma \Rightarrow B \leq \sqrt{2\mu_0 \Sigma} = \sqrt{2 \times 4\pi \times 10^{-7} \times 70 \times 10^6} = 13 \text{ T}$$

$$\Rightarrow W_B = \frac{1}{2} \mu_0 B^2 = \frac{1}{2} \times 4\pi \times 10^{-7} \times 13^2 \Rightarrow W_B = \frac{1}{2} \frac{B^2}{\mu_0} = \frac{1}{2} \frac{13^2}{4\pi \times 10^{-7}} = 6.7 \times 10^7 \text{ J/m}^3 = 67000 \text{ kJ/m}^3$$

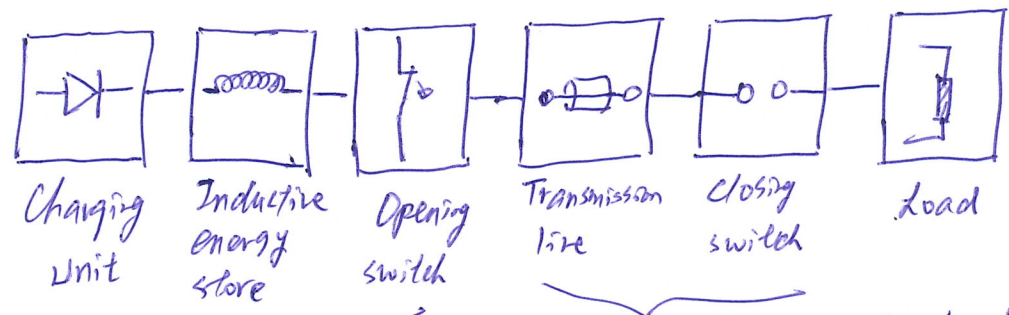
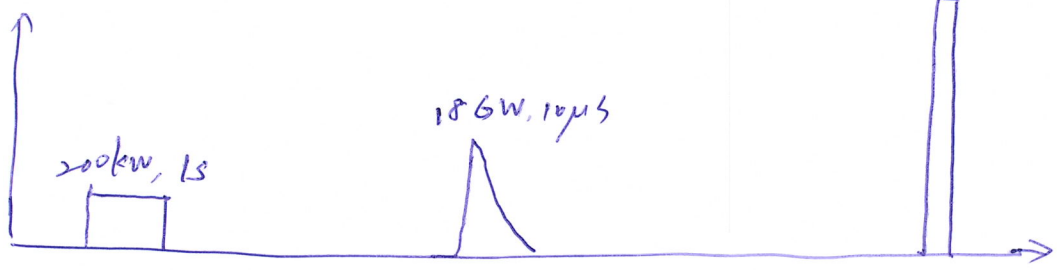
\Rightarrow The energy density stored in a magnetic field can be about 2 orders of magnitude higher than that storable in an electric field !!

- * Capacitive storage - requires one or more closing switches which remain open during charging and hold the charging voltage.
- power multiplication is done by current amplification.
- * Inductive storage - requires an opening switch which is closed during charge-up, carrying a large current at this stage.
- power multiplication is done by voltage amplification.

Capacitive storage $w_e = 10 - 30 \text{ kJ/m}^3$

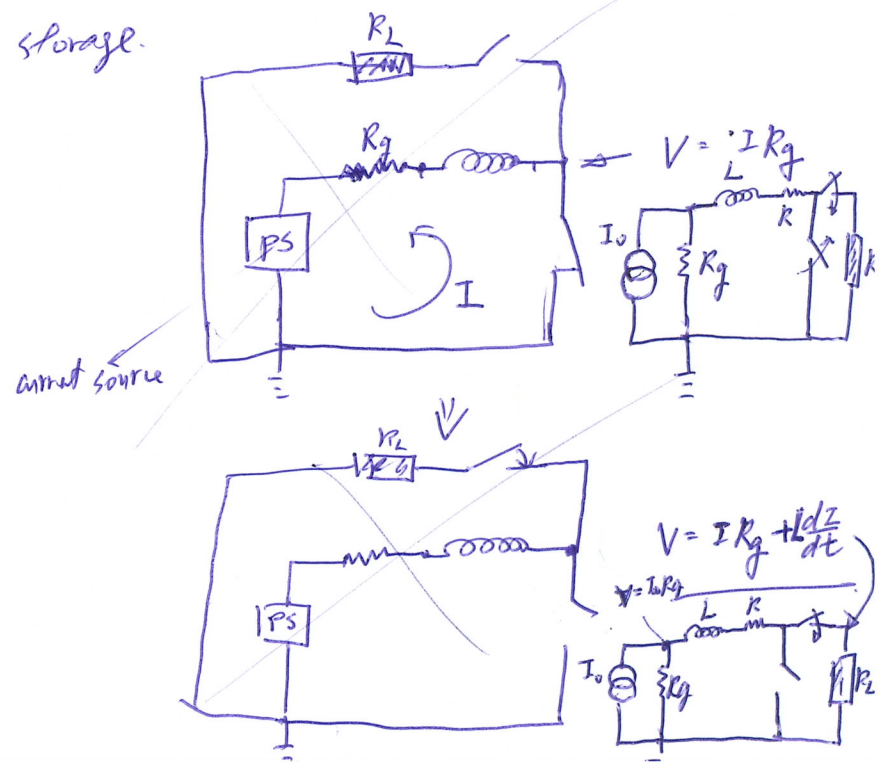
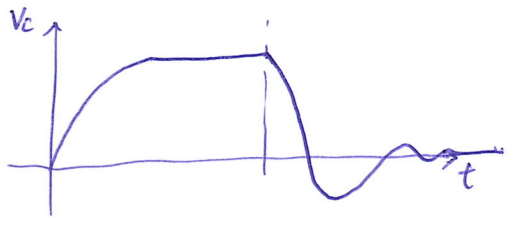
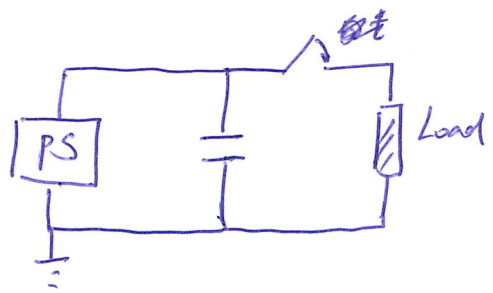


Inductive storage $w_m = 1 - 50 \text{ MJ/m}^3$



1. Compressing stage
2. Compressing stage (pulse forming line)

Example of Capacitive storage.



Review of circuit analysis

P10

* Kirchhoff's Current Law.

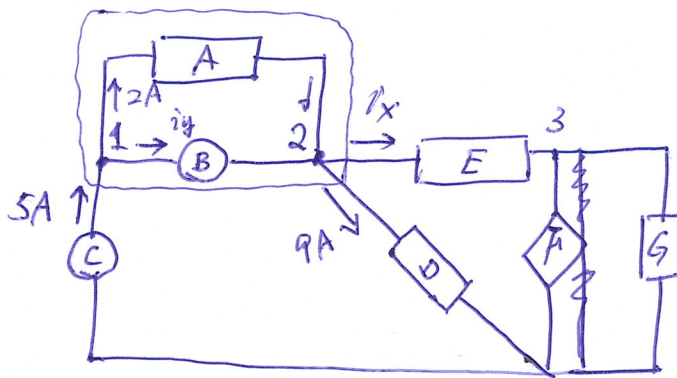
- At any instant in time, the algebraic sum of all currents leaving any closed surface is zero

$$i_1 + i_2 + \dots + i_N = 0,$$

or in abbreviated notation:

$$\sum_{k=1}^N i_k = 0$$

where i_k is the k^{th} current of the N currents leaving the closed surfaces.



$$\begin{aligned} i_y + 2 - 5 &= 0 \\ \Rightarrow i_y &= 3 \text{ (A)} \\ -5 + i_x + 9 &= 0 \\ \Rightarrow i_x &= -4 \text{ (A)} \end{aligned}$$

* Kirchhoff's Voltage Law.

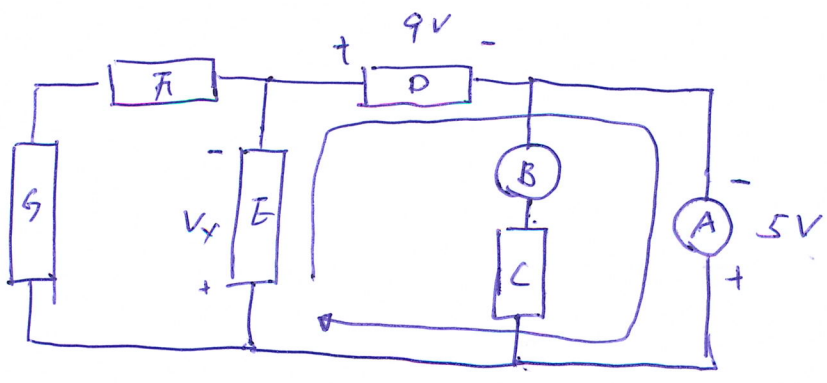
- At any instant in time, the algebraic sum of all voltage drops taken around any closed path is 0:

$$V_1 + V_2 + \dots + V_N = 0.$$

or in abbreviated notation:

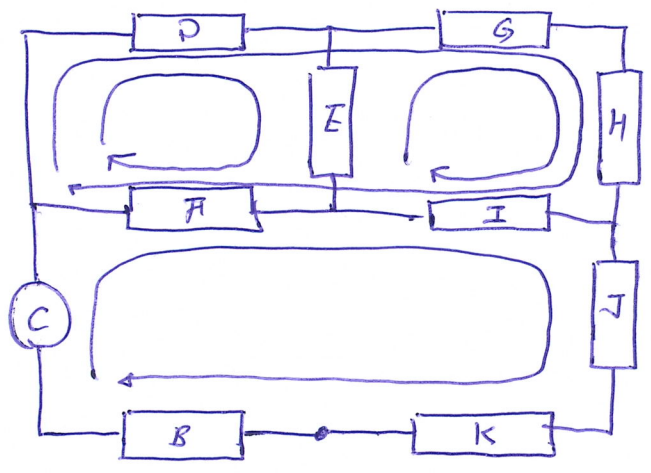
$$\sum_{k=1}^N V_k = 0$$

where V_k is the voltage drop, taken in the direction of the path along the k^{th} segment of the N segments in the closed path.

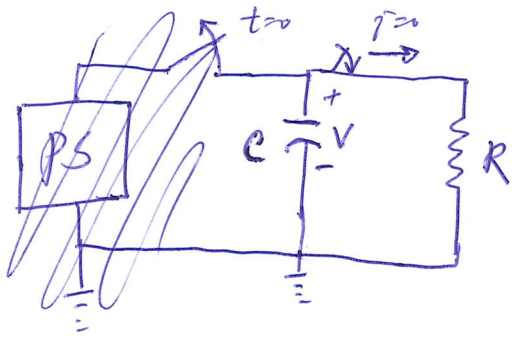


$$-V_x - 9 + 5 = 0 \Rightarrow \underline{V_x = -4V}$$

* Loops, Meshes, and Planar Networks



* Source-free RC circuit.



~~* Assumng~~
 * Assumng that the capacitor is fully charged to V_0 .
 At t_0 , the switch is opened

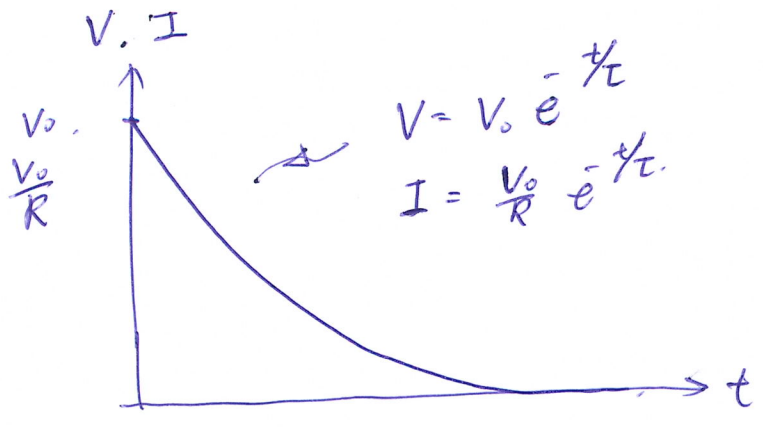
$$V_c - IR = 0 \quad I = \frac{dQ}{dt} = -C \frac{dV}{dt} \quad C = \frac{Q}{V}$$

$$\Rightarrow V_c + RC \frac{dV}{dt} = 0 \quad \text{or} \quad \frac{dV}{dt} + \frac{1}{RC} V = 0$$

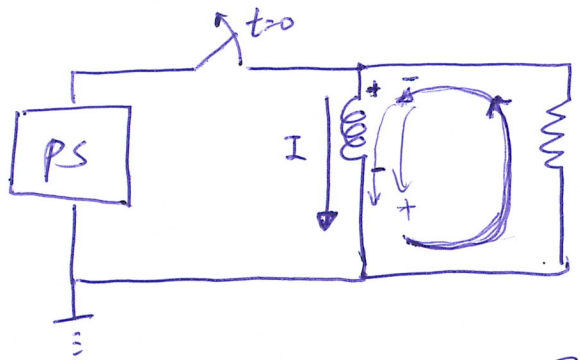
$$\Rightarrow \int_{V_0}^V \frac{dV}{V} = -\frac{1}{RC} \int_0^t dt \Rightarrow \ln \frac{V(t)}{V_0} = -\frac{t}{RC}$$

$$\Rightarrow V(t) = V_0 e^{-\frac{t}{RC}} = \frac{V_0 e^{-\frac{t}{RC}}}{1} \quad \tau = RC$$

$$I = -C \frac{dV}{dt} = +V_0 C \left(+\frac{1}{\tau} \right) e^{-\frac{t}{\tau}} = \frac{V_0}{R} e^{-\frac{t}{\tau}}$$



* Source-free RL circuit



* Assuming the current is at steady state for $t \leq 0$, $I(0) = I_0$
At t_0 , the switch is opened

~~$V_L = IR + V_L = 0 \Rightarrow L \frac{dI}{dt} = 0$~~

$$-IR - V_L = 0 \quad V_L = L \frac{dI}{dt}$$

$$\Rightarrow IR + L \frac{dI}{dt} = 0 \quad \Rightarrow \frac{dI}{dt} + \frac{R}{L} I = 0$$

$$\Rightarrow \int \frac{dI}{I} = -\frac{R}{L} \int dt \quad \Rightarrow \ln \frac{I(t)}{I(0)} = -\frac{R}{L} t = -\frac{t}{\tau_L} \quad \tau_L = \frac{L}{R}$$

$$\Rightarrow I(t) = I_0 e^{-\frac{R}{L} t} = I_0 e^{-\frac{t}{\tau_L}}$$

$$V(t) = L \frac{dI}{dt} = L \cdot I_0 \cdot \left(-\frac{1}{\tau_L}\right) e^{-\frac{t}{\tau_L}}$$

$$= -RI_0 e^{-\frac{t}{\tau_L}}$$

